

PATENT

Docket No.: ACT-307DVA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Art Unit: 2814

Examiner: Mai, Anh D.

Serial No.: 10/036,303

Filed: December 28, 2001

In Re Application of: Hawley, et al.

For:

METHOD FOR FABRICATING AN MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT

Certificate of Mailing

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail, in an envelope addressed to MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

TRANSMITTAL LETTER

mendment
hissioner for Patents
Box 1450
ndria, VA 22313-1450

Sir:

In response to the Office Action dated December 26, 2002, in the above 8 identified application, enclosed please find the following:

- Response to Office Action/Amendment; 1.
- 2. Declaration Under 37 CFR 1.132;
- 2. Request for Extension of Time; and
- 3. Check in the amount of \$410.00 calculated as follows for a large entity:

2 month extension of time

\$410.00

TOTAL:

\$410.00

In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, the Assistant

PATENT :

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Commissioner is hereby authorized to charge or credit the difference to our

Deposit Account No. 50-0612. A duplicate of this transmittal is enclosed.

Dated:

Sierra Patent Group, Ltd. PO Box 6149 Stateline, NV 89449

(775) 586-9500

Respectfully submitted, Signa Parent Group, Ltd.

Reg. No. 47,208